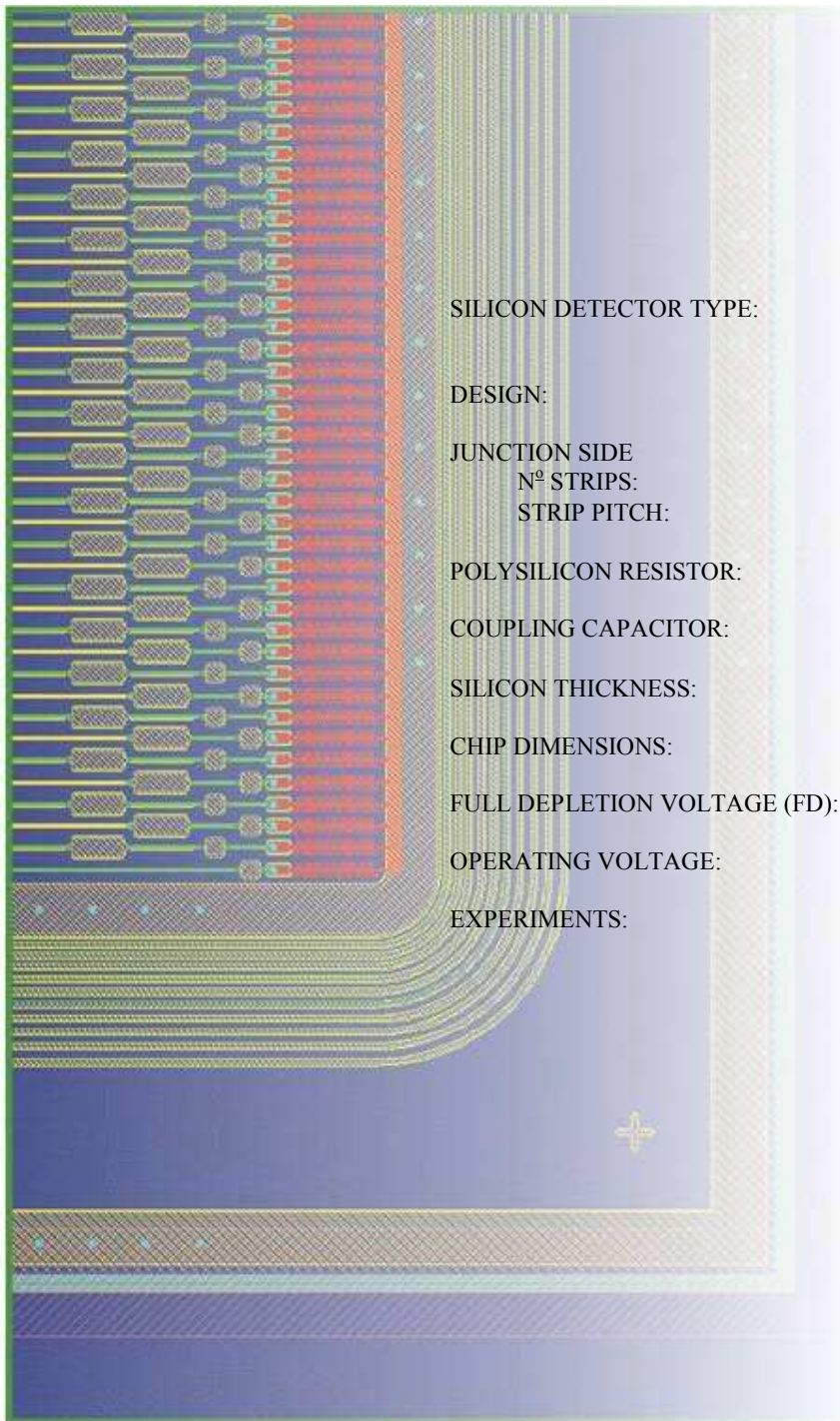
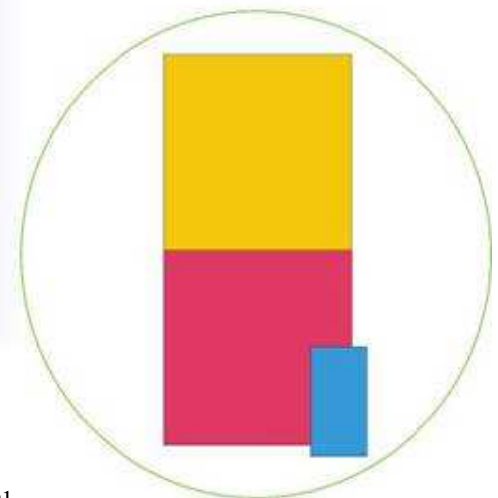


AC COUPLED ION IMPLANTED TOTALLY DEPLETED SINGLE SIDED MICROSTRIP DETECTOR WITH MULTI-GUARDRING DESIGN FOR HIGH RADIATION ENVIRONMENT



SILICON DETECTOR TYPE:	AC coupled ion implanted totally depleted silicon microstrip detector.
DESIGN:	Single sided, multi-guard ring design for high radiation environment, 6 inch wafer technology.
JUNCTION SIDE N° STRIPS:	1024 + 2
STRIP PITCH:	61 μm
POLYSILICON RESISTOR:	4.5 ± 0.5 MΩ
COUPLING CAPACITOR:	100 pF
SILICON THICKNESS:	300 ± 10 μm
CHIP DIMENSIONS:	62.6 x 60.3 mm ²
FULL DEPLETION VOLTAGE (FD):	50 V maximum
OPERATING VOLTAGE:	FD to 2FD
EXPERIMENTS:	CMS, CERN



QUALITY ASSURANCE :ISO9001

